Silicon PNP Power Transistors 2SB731

DESCRIPTION

·With TO-126 package
·Complement to type 2SD809
·Low collector saturation voltage

APPLICATIONS

·Audio frequency power amplifier
·Low speed switching

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

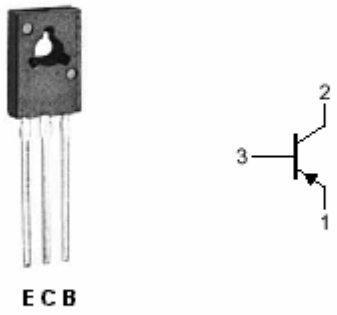

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-1	A
I_{CM}	Collector current-Peak		-2	A
I_B	Base current (DC)		-0.5	A
P_T	Total power dissipation	T_a=25□	1.0	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1.0A; I_B=-50mA		-0.5	-0.6	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1.0A; I_B=-50mA		-1.0	-1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=-50V; I_E=0			-0.1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-6V; I_C=0			-0.1	μA
h_{FE-1}	DC current gain	I_C=-0.1A ; V_{CE}=-2V	135		600	
h_{FE-2}	DC current gain	I_C=-1A ; V_{CE}=-1V	40			
f_T	Transition frequency	I_C=-10mA ; V_{CE}=-2V		75		MHz
C_{OB}	Collector output capacitance	I_E=0; f=1MHz ; V_{CB}=-10V		25		pF

◆ **h_{FE-1} Classifications**

L	K	F	E
135-270	200-400	300-480	360-600

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PACKAGE OUTLINE

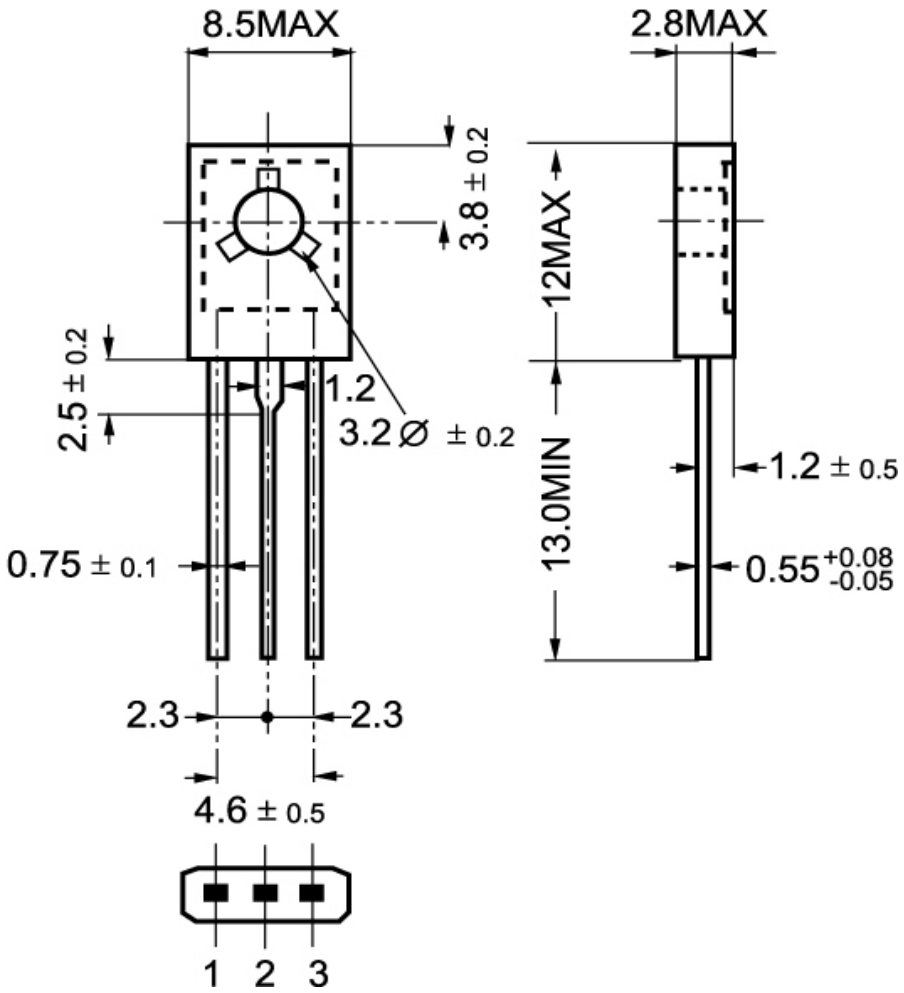

Fig.2 Outline dimensions